

### **80V NPN DARLINGTON TRANSISTOR IN SOT23**

#### **Features**

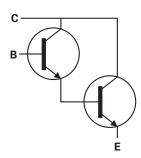
- BV<sub>CES</sub> > 80V
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- High Current Gain
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

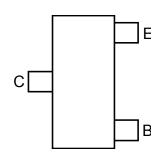
- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>3</a>
- Weight 0.008 grams (approximate)







Device Symbol



Top View Pin-Out

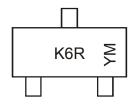
## Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBTA28-7-F	AEC-Q101	K6R	7	8	3,000
MMBTA28-13-F	AEC-Q101	K6R	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



K6R = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: B = 2014) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

	Year	2010		2011	2012		2013	2014		2015	2016	i	2017
	Code	Х		Υ	Z		Α	В		С	D		Е
1	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	80	V
Collector-Emitter Voltage	V <sub>CES</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	12	V
Continuous Collector Current	Ic	500	mA

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

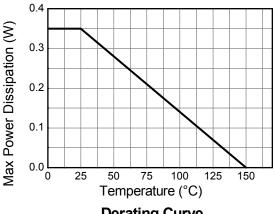
Characteristic		Symbol	Value	Unit	
Dower Dissination	(Note 5)	0	310	mW	
Power Dissipation	(Note 6)	$P_{D}$	350		
Thermal Desistance Junction to Ambient	(Note 5)	0	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	357	-C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

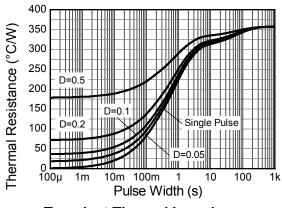
Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

  6. Same as note (5), except the device is mounted on 15 mm x 15mm 1oz copper.

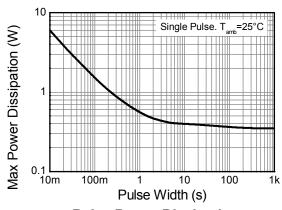
  7. Thermal resistance from junction to solder-point (at the end of the leads).





## **Derating Curve**

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80	_	_	V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CES</sub>	80	_	_	V	$I_C = 100 \mu A, V_{BE} = 0$	
Emitter-Base Breakdown Voltage	$BV_{EBO}$	12	_	_	V	$I_E = 100 \mu A, I_C = 0$	
Collector cut-off current	I <sub>CBO</sub>	_		100	nA	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0	
Collector cut-on current	I <sub>CES</sub>	_	_	500	nA	V <sub>CE</sub> = 60V, V <sub>BE</sub> = 0	
Emitter-base Cut-off Current	I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 10V, I <sub>C</sub> = 0	
ON CHARACTERISTICS (Note 8)							
Static Forward Current Transfer Ratio	h <sub>FE</sub>	10,000	_	_	_	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V	
Static Folward Current Transfer Ratio		10,000				$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}$	
Collector-Emitter Saturation Voltage	Vor. "	_	_	1.2	V	$I_C = 10 \text{mA}, I_B = 10 \mu \text{A}$	
Concetor-Emitter Cataration Voltage	V <sub>CE(sat)</sub>			1.5	٧	$I_C = 100 \text{mA}, I_B = 100 \mu \text{A}$	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	_		2.0	V	$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}$	
SMALL SIGNAL CHARACTERISTICS (Note 8)							
Current Gain-Bandwidth Product	f⊤	125	_	_	MHz	$I_C = 10$ mA, $V_{CE} = 5$ V,	
	•	1.20				f = 100MHz	
Output Capacitance	$C_{obo}$	_	8.0	_	pF	$V_{CB} = 10V, f = 1MHz, I_{E} = 0$	
Input Capacitance	$C_{ibo}$	_	15.0	_	pF	$V_{EB} = 0.5V, f = 1MHz, I_{C} = 0$	

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

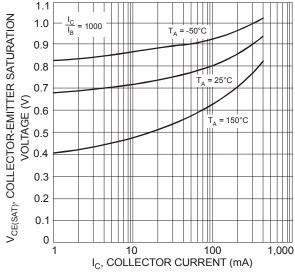
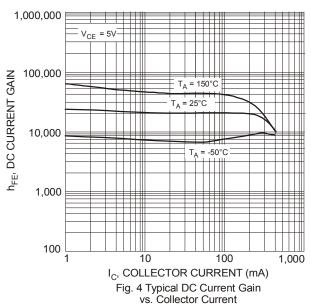


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current



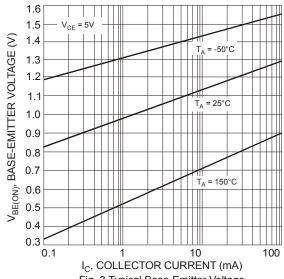


Fig. 3 Typical Base-Emitter Voltage vs. Collector Current

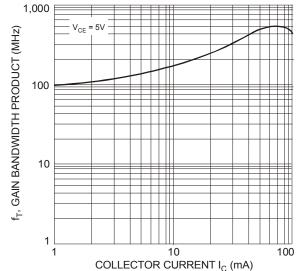
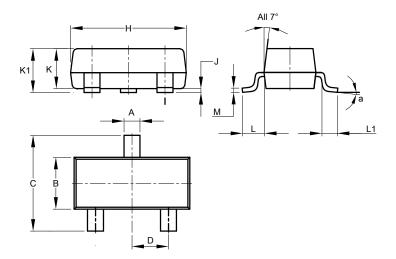


Fig. 5 Typical Gain Bandwidth Product vs. Collector Current



# **Package Outline Dimensions**

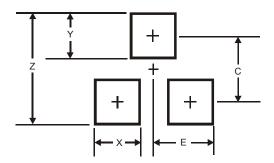
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Ι	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	a 8°						
All Dimensions in mm							

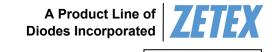
## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35





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